

N-Channel Enhancement-Mode MOSFET

DESIGNED FOR:

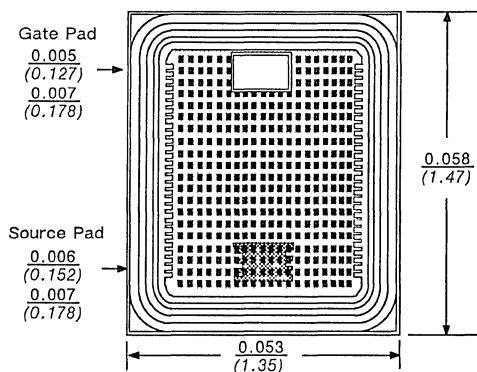
- Switching
- Amplification

FEATURES

- High Breakdown > 400 V
- Low $r_{DS(on)} < 12 \Omega$

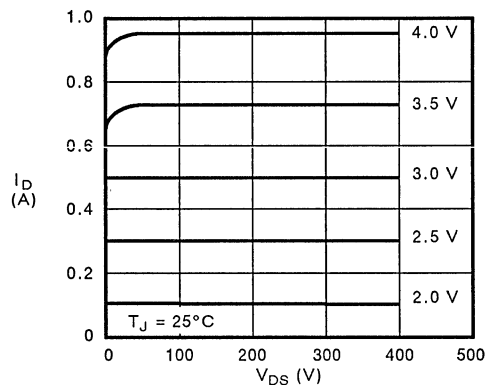
TYPE	PACKAGE	DEVICE
Single	TO-205AD	• VN4012B
	TO-92	• VN3515L, VN4012L
	Chip	• Available as above specifications

GEOMETRY DIAGRAM

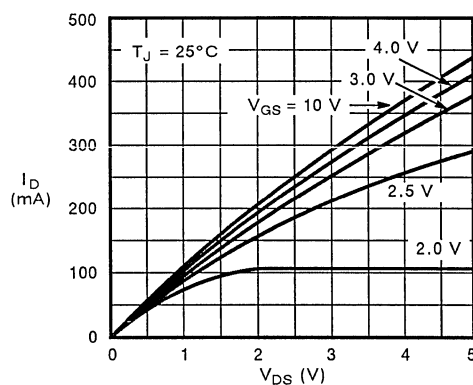


TYPICAL CHARACTERISTICS

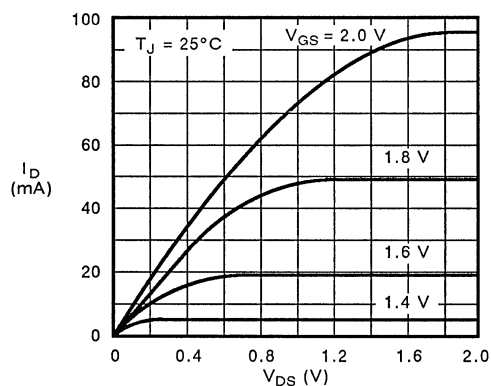
Output Characteristics



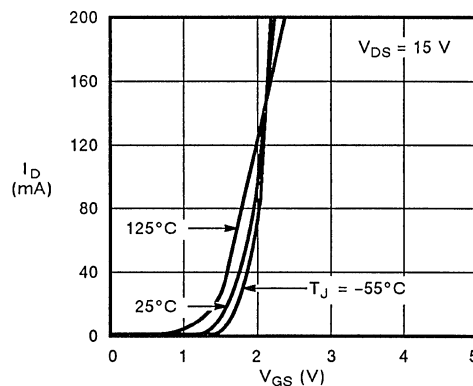
Ohmic Region Characteristics



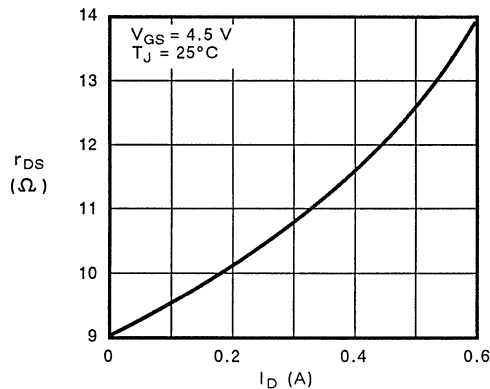
Output Characteristics for Low Gate Drive



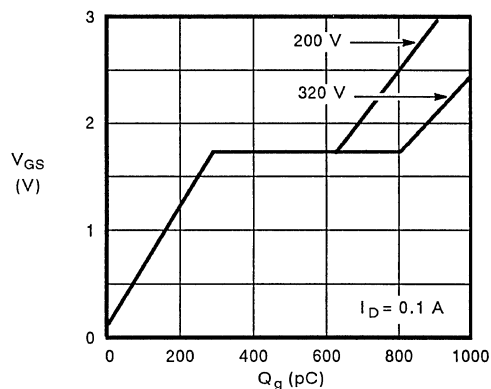
Transfer Characteristics



On-Resistance

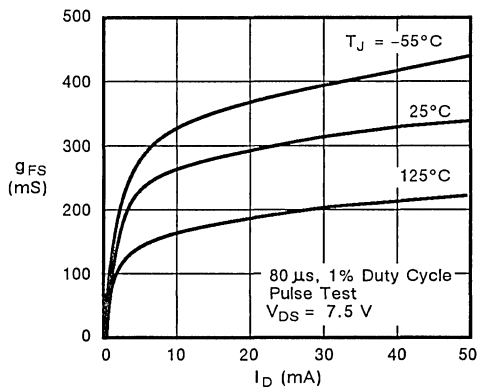


Gate Charge

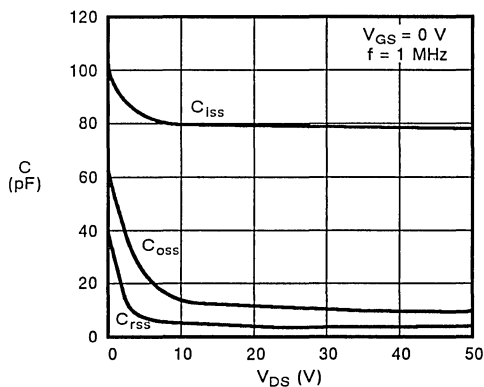


TYPICAL CHARACTERISTICS

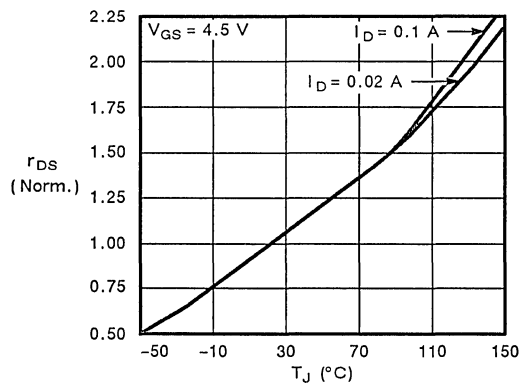
Transconductance



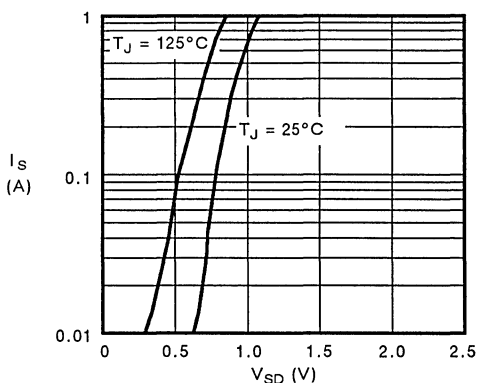
Capacitance



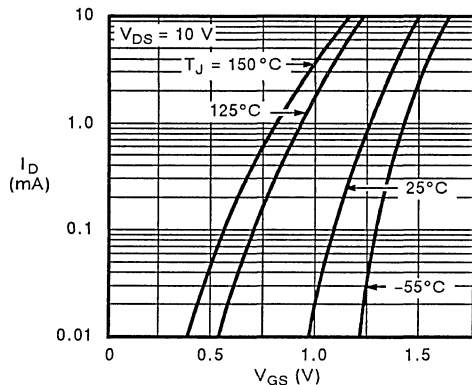
On-Resistance vs. Junction Temperature



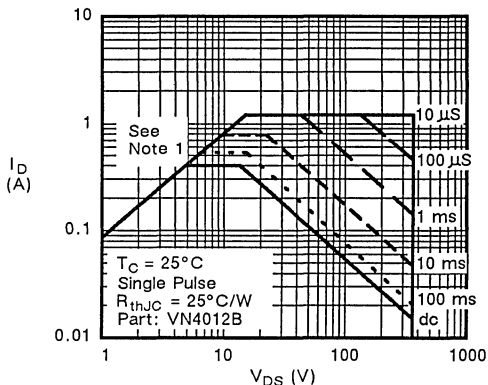
Source-Drain Diode Forward Voltage



Threshold Region

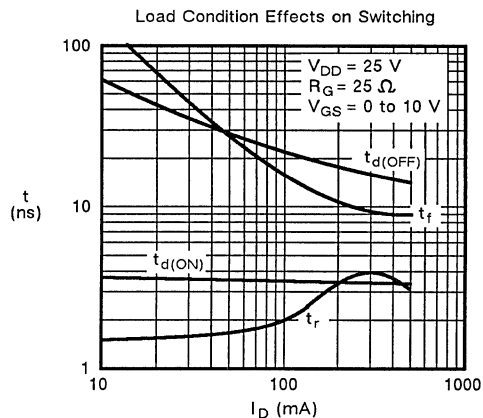
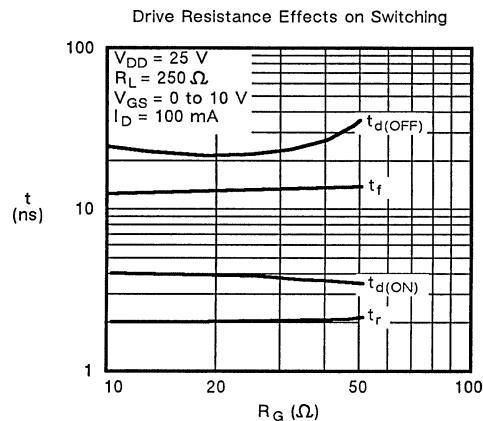
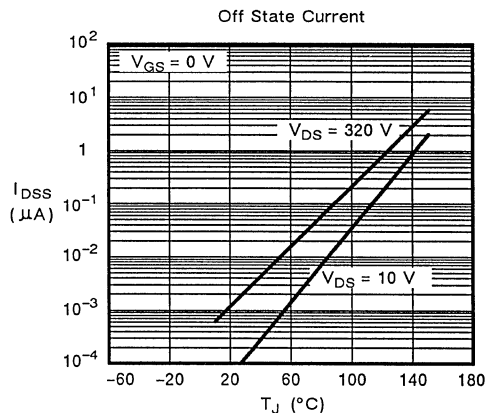
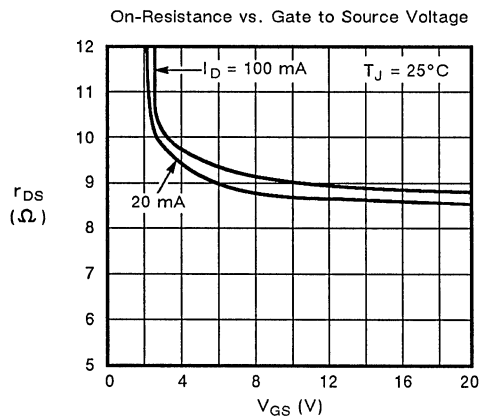
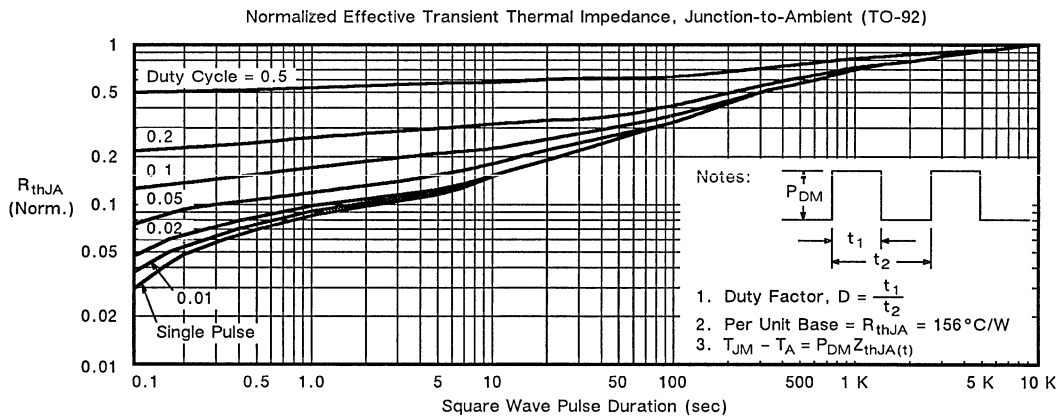


Safe Operating Area



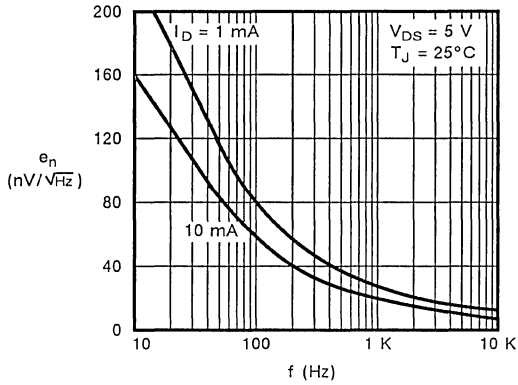
¹Operation in this area may be limited by $r_{DS(ON)}$

TYPICAL CHARACTERISTICS

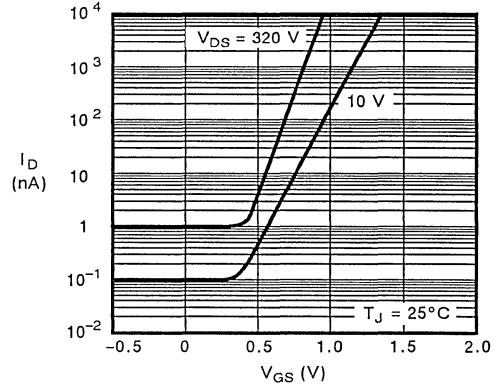


TYPICAL CHARACTERISTICS

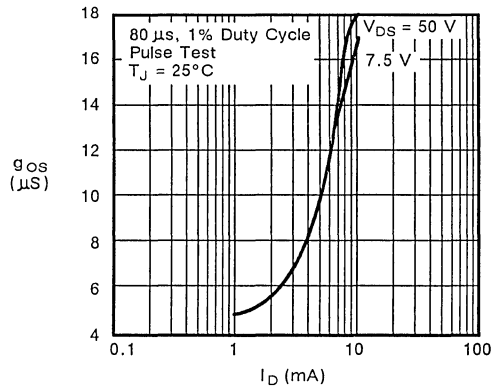
Equivalent Input Noise Voltage vs. Frequency



Body-Drain Leakage Current



Output Conductance vs. Drain Current



Transient Thermal Response (TO-205AF)

